

MBRD620CTG Series, NRVBD640CTG Series

SWITCHMODE Power Rectifiers

DPAK-3 Surface Mount Package

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- Extremely Fast Switching
- Extremely Low Forward Drop
- Platinum Barrier with Avalanche Guardrings
- NRVBD Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant*

Mechanical Characteristics:

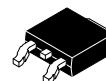
- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Ratings:
 - ♦ Machine Model = C
 - ♦ Human Body Model = 3B



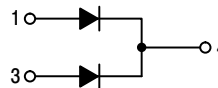
ON Semiconductor®

<http://onsemi.com>

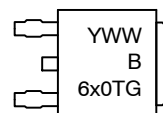
SCHOTTKY BARRIER RECTIFIERS 6.0 AMPERES, 20 – 60 VOLTS



**DPAK
CASE 369C**



MARKING DIAGRAM



Y	= Year
WW	= Work Week
B6x0T	= Device Code
x	= 2, 3, 4, 5, or 6
G	= Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS

Rating	Symbol	MBRD/NRVBD/SBR					Unit
		620CT	630CT	640CT	650CT	660CT	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	50	60	V
Average Rectified Forward Current $T_C = 130^\circ\text{C}$ (Rated V_R) Per Diode Per Device	$I_{F(AV)}$	3 6					A
Peak Repetitive Forward Current, $T_C = 130^\circ\text{C}$ (Rated V_R , Square Wave, 20 kHz) Per Diode	I_{FRM}	6					A
Nonrepetitive Peak Surge Current – (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	75					A
Peak Repetitive Reverse Surge Current (2 μs , 1 kHz)	I_{RRM}	1					A
Operating Junction Temperature (Note 1)	T_J	–65 to +175					$^\circ\text{C}$
Storage Temperature	T_{stg}	–65 to +175					$^\circ\text{C}$
Voltage Rate of Change (Rated V_R)	dv/dt	10,000					V/ μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	6	$^\circ\text{C}/\text{W}$
Maximum Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	80	$^\circ\text{C}/\text{W}$

2. Rating applies when surface mounted on the minimum pad size recommended.

ELECTRICAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3) $i_F = 3$ Amps, $T_C = 25^\circ\text{C}$ $i_F = 3$ Amps, $T_C = 125^\circ\text{C}$ $i_F = 6$ Amps, $T_C = 25^\circ\text{C}$ $i_F = 6$ Amps, $T_C = 125^\circ\text{C}$	V_F	0.7 0.65 0.9 0.85	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, $T_C = 25^\circ\text{C}$) (Rated dc Voltage, $T_C = 125^\circ\text{C}$)	i_R	0.1 15	mA

3. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

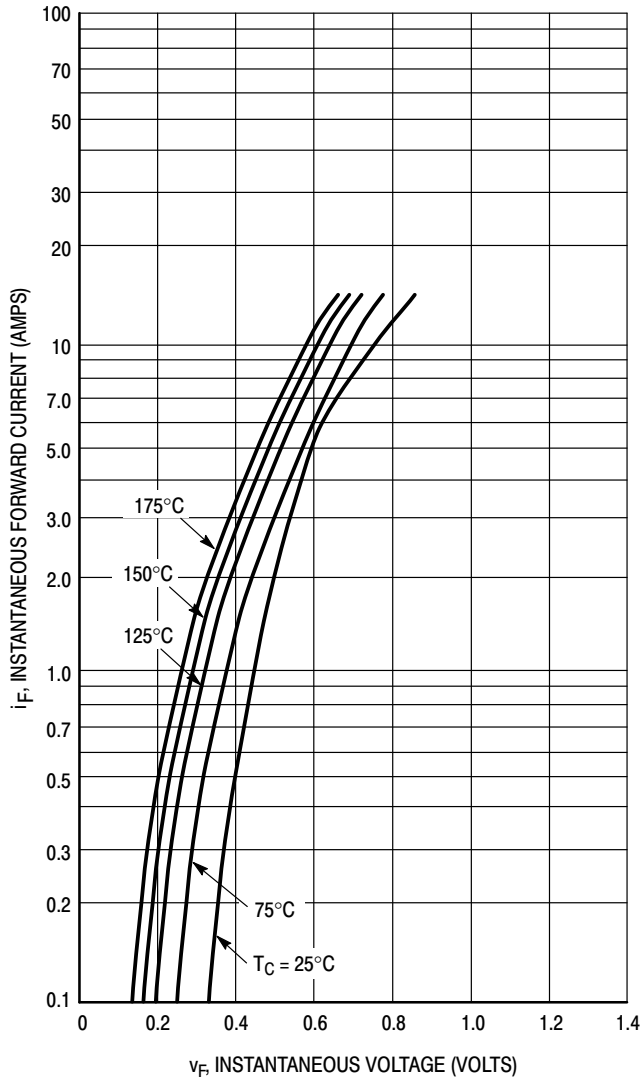
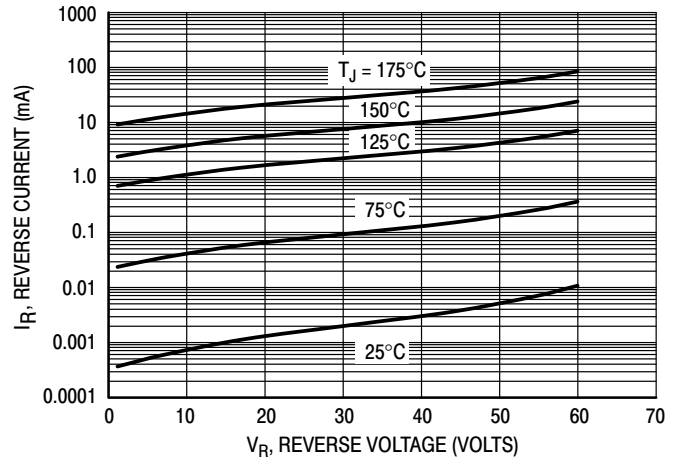


Figure 1. Typical Forward Voltage, Per Leg



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R .

Figure 2. Typical Reverse Current, * Per Leg

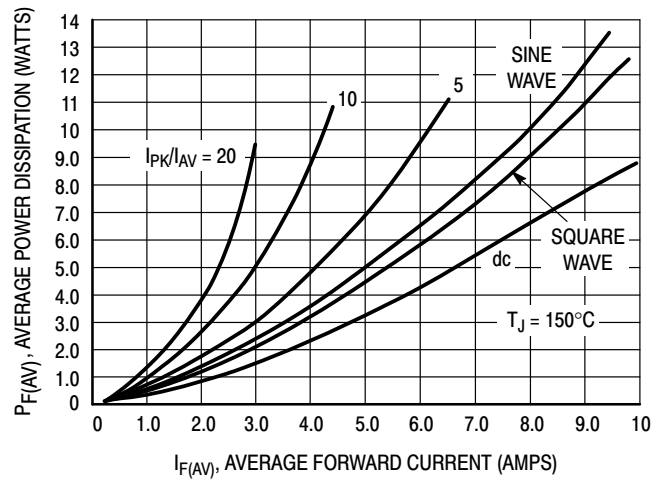


Figure 3. Average Power Dissipation, Per Leg

TYPICAL CHARACTERISTICS

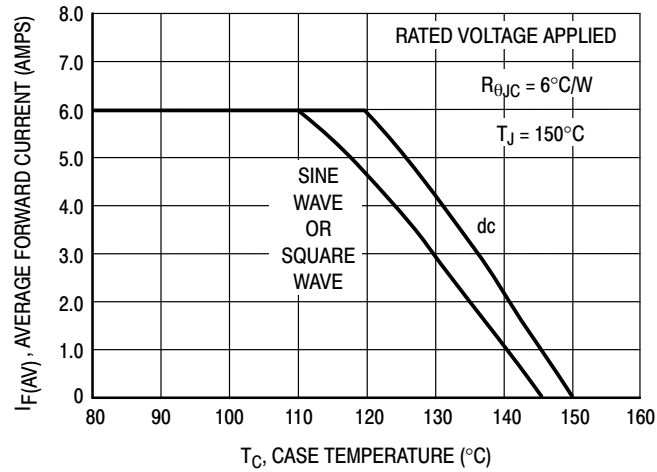


Figure 4. Current Derating, Case, Per Leg

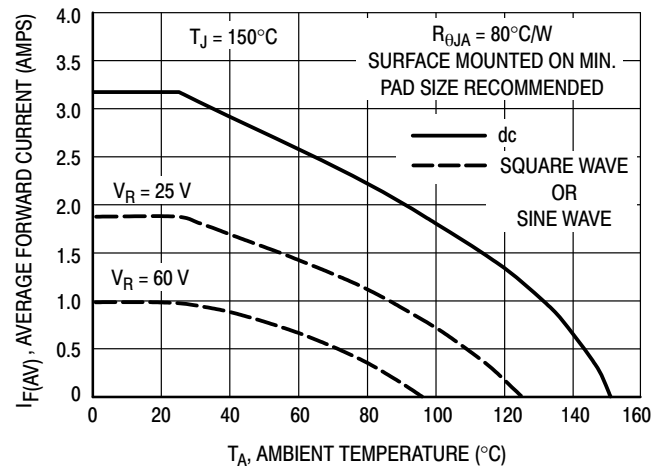


Figure 5. Current Derating, Ambient, Per Leg

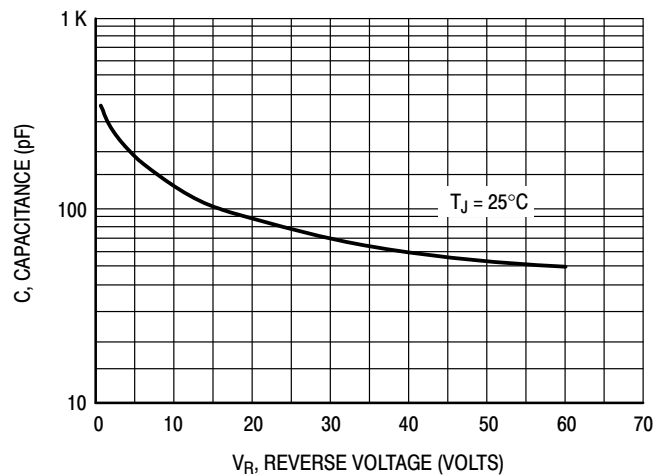


Figure 6. Typical Capacitance, Per Leg

MBRD620CTG Series, NRVBD640CTG Series

ORDERING INFORMATION

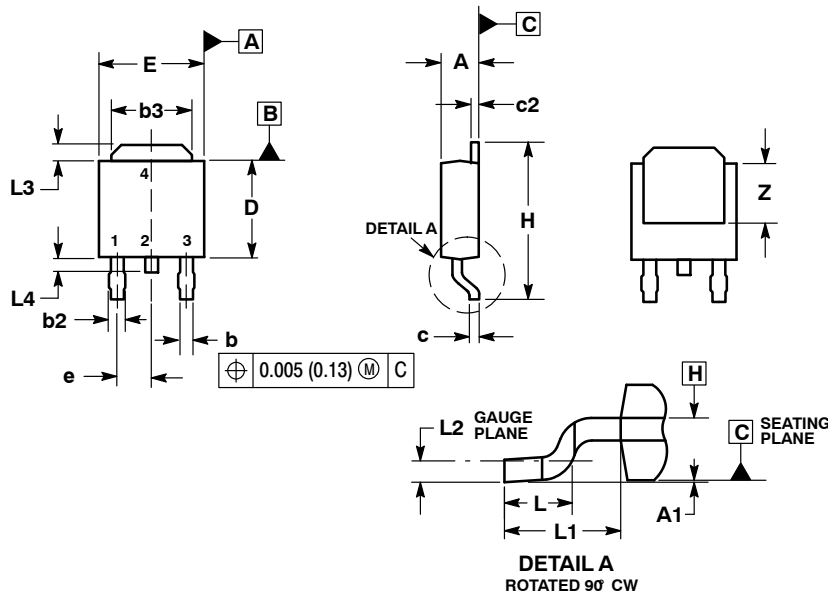
Device	Package	Shipping [†]
MBRD620CTT4G	DPAK (Pb-Free)	2500 / Tape & Reel
MBRD630CTT4G		2500 / Tape & Reel
MBRD640CTG		75 Units / Rail
NRVBD640CTG		75 Units / Rail
MBRD640CTT4G		2500 / Tape & Reel
NRVBD640CTT4G		2500 / Tape & Reel
MBRD650CTG		75 Units / Rail
MBRD650CTT4G		2500 / Tape & Reel
NRVBD650CTT4G		2500 / Tape & Reel
MBRD660CTG		75 Units / Rail
NRVBD660CTG		75 Units / Rail
MBRD660CTRLG		1800 / Tape & Reel
MBRD660CTT4G		2500 / Tape & Reel
NRVBD660CTT4G		2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE D

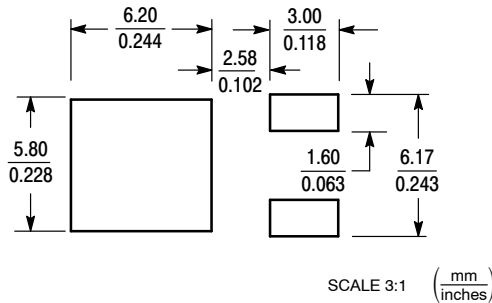


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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